

## IN THE CLAIMS

Please amend the claims as follows:

Please amend claims 1, 10 and 19 as follows:

1. (Amended) A particle, comprising:  
a semiconductor nanocrystal,  
wherein said nanocrystal is doped with a carrier selected from the group  
consisting of an electron and a hole.

10. (Amended) A method of making a particle, comprising:  
adding at least one carrier to a semiconductor nanocrystal, to form a  
doped semiconductor nanocrystal;  
wherein said carrier is selected from the group consisting of an electron  
and a hole.

19. (Amended) The method of claim 10, wherein said particle comprises  
capping groups, on the surface of said nanocrystal.

Please add new claims 34 - 42 as follows:

34. The particle of claim 1, wherein said nanocrystal comprises sodium.

35. The particle of claim 5, wherein said nanocrystal comprises sodium.

36. The particle of claim 35, further comprising trioctylphosphine oxide  
capping groups on a surface of said nanocrystal.

37. The particle of claim 8, wherein said capping groups comprise  
trioctylphosphine oxide.

38. The method of claim 10, wherein said adding comprises contacting said semiconductor nanocrystal with a reducing agent, said reducing agent comprising sodium.

39. The method of claim 38, wherein said reducing agent comprises sodium biphenyl.

40. The method of claim 11, wherein said adding further comprises contacting said semiconductor nanocrystal with a charge shuttle.

41. The method of claim 16, wherein said adding comprises contacting said semiconductor nanocrystal with a reducing agent, said reducing agent comprising sodium.

42. The method of claim 41, wherein said reducing agent comprises sodium biphenyl.